

MM54HC521/MM74HC521 8-Bit Magnitude Comparator (Equality Detector)

General Description

This equality detector utilizes advanced silicon-gate CMOS technology to compare bit for bit two 8-bit words and indicates whether or not they are equal. The $\overline{P=Q}$ output indicates equality when it is low. A single active low enable is provided to facilitate cascading of several packages and enable comparison of words greater than 8 bits.

This device is useful in memory block decoding applications, where memory block enable signals must be generated from computer address information.

The comparator's output can drive 10 low power Schottky equivalent loads. This comparator is functionally and pin

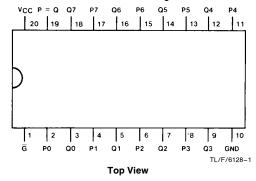
compatible to the 54LS688/74LS688 and the 54HC688/74HC688. All inputs are protected from damage due to static discharge by diodes to V_{CC} and ground.

Features

- Typical propagation delay: 20 ns
- Wide power supply range: 2-6V
- Low quiescent current: 80 µA (74 Series)
- Large output current: 4 mA (74 Series)
- Identical to 'HC688

Connection and Logic Diagrams

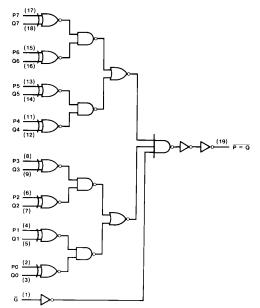
Dual-In-Line Package



Order Number MM54HC521 or MM74HC521

Truth Table

| Inp | | | | |
|-------|-------------|-------------------------------|--|--|
| Data | | | | |
| P,Q | Enable G | $\overline{P} = \overline{Q}$ | | |
| P = Q | L | L | | |
| P > Q | L | Н | | |
| P < Q | L | Н | | |
| Х | Н | Н | | |



TL/F/6128-2

Absolute Maximum Ratings (Notes 1 and 2)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/Distributors for availability and specifications.

| Supply Voltage (V _{CC}) | -0.5 to $+7.0$ V |
|---|-------------------------------|
| DC Input Voltage (V _{IN}) | -1.5 to V _{CC} +1.5V |
| DC Output Voltage (V _{OUT}) | -0.5 to $V_{CC} + 0.5V$ |
| Clamp Diode Current (I _{IK} , I _{OK}) | \pm 20 mA |
| DC Output Current, per pin (IOUT) | \pm 25 mA |
| DC V _{CC} or GND Current, per pin (I _{CC}) | \pm 50 mA |
| Storage Temperature Range (T _{STG}) | -65°C to +150°C |

Power Dissipation (P_D)

(Note 3) 600 mW S.O. Package only 500 mW

Lead Temperature (T_L)

(Soldering 10 seconds) 260°C

Operating Conditions

| Min | Max | Units |
|-----|---------------|--|
| 2 | 6 | V |
| 0 | V_{CC} | V |
| | | |
| -40 | +85 | °C |
| -55 | +125 | °C |
| | | |
| | 1000 | ns |
| | 500 | ns |
| | 400 | ns |
| | 2 0 -40 | 2 6 0 V _{CC} -40 +85 -55 +125 1000 500 |

DC Electrical Characteristics (Note 4)

| Symbol | Parameter | Conditions | v _{cc} | T _A = | = 25°C | 74HC T _A = -40 to 85°C | 54HC T _A = -55 to 125°C | Units |
|-----------------|-------------------------------------|--|-----------------|-----------------------|--------|--------------------------------------|---------------------------------------|-------|
| | | | | Typ Guaranteed Limits | | | | |
| V_{IH} | Minimum High Level | | 2.0V | | 1.5 | 1.5 | 1.5 | V |
| | Input Voltage | | 4.5V | | 3.15 | 3.15 | 3.15 | V |
| | | | 6.0V | | 4.2 | 4.2 | 4.2 | V |
| V_{IL} | Maximum Low Level | | 2.0V | 1 | 0.5 | 0.5 | 0.5 | V |
| | Input Voltage** | | 4.5V | | 1.35 | 1.35 | 1.35 | V |
| | | | 6.0V | | 1.8 | 1.8 | 1.8 | V |
| V_{OH} | Minimum High Level | V _{IN} = V _{IH} or V _{IL} | | | | | | |
| | Output Voltage | I _{OUT} ≤20 μA | 2.0V | 2.0 | 1.9 | 1.9 | 1.9 | V |
| | | | 4.5V | 4.5 | 4.4 | 4.4 | 4.4 | V |
| | | | 6.0V | 6.0 | 5.9 | 5.9 | 5.9 | V |
| | | $V_{IN} = V_{IH}$ or V_{IL} | 1 | | | | | |
| | | I _{OUT} ≤4.0 mA | 4.5V | 4.2 | 3.98 | 3.84 | 3.7 | V |
| | | I _{OUT} ≤5.2 mA | 6.0V | 5.7 | 5.48 | 5.34 | 5.2 | V |
| V_{OL} | Maximum Low Level | V _{IN} = V _{IH} or V _{IL} | | | | | | |
| | Output Voltage | I _{OUT} ≤20 μA | 2.0V | 0 | 0.1 | 0.1 | 0.1 | V |
| | | | 4.5V | 0 | 0.1 | 0.1 | 0.1 | V |
| | | | 6.0V | 0 | 0.1 | 0.1 | 0.1 | V |
| | | V _{IN} = V _{IH} or V _{IL} | | | | | | |
| | | I _{OUT} ≤4.0 mA | 4.5V | 0.2 | 0.26 | 0.33 | 0.4 | V |
| | | I _{OUT} ≤5.2 mA | 6.0V | 0.2 | 0.26 | 0.33 | 0.4 | V |
| I _{IN} | Maximum Input Current | V _{IN} =V _{CC} or GND | 6.0V | | ±0.1 | ±1.0 | ±1.0 | μΑ |
| Icc | Maximum Quiescent Supply Current | $V_{IN} = V_{CC}$ or GND $I_{OUT} = 0 \mu A$ | 6.0V | | 8.0 | 80 | 160 | μΑ |

Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.

Note 2: Unless otherwise specified all voltages are referenced to ground.

Note 3: Power Dissipation temperature derating — plastic "N" package: -12 mW/°C from 65°C to 85°C; ceramic "J" package: -12 mW/°C from 100°C to 125°C.

Note 4: For a power supply of 5V $\pm 10\%$ the worst case output voltages (V_{CH}, and V_{CL}) occur for HC at 4.5V. Thus the 4.5V values should be used when designing with this supply. Worst case V_{IH} and V_{IL} occur at V_{CC}=5.5V and 4.5V respectively. (The V_{IH} value at 5.5V is 3.85V.) The worst case leakage current (I_{IN}, I_{CC}, and I_{OZ}) occur for CMOS at the higher voltage and so the 6.0V values should be used.

^{**} V_{IL} limits are currently tested at 20% of V_{CC} . The above V_{IL} specification (30% of V_{CC}) will be implemented no later than Q1, CY'89.

AC Electrical Characteristics

 $V_{CC} = 5V$, $T_A = 25$ °C, $C_L = 15$ pF, $t_r = t_f = 6$ ns

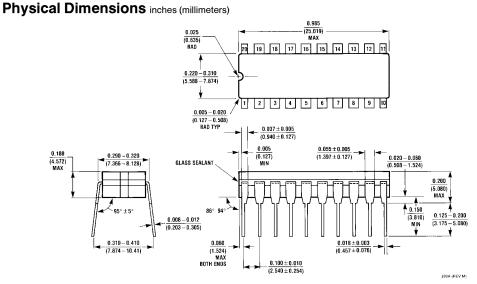
| Symbol | Parameter | Conditions | Тур | Guaranteed Limit | Units |
|-------------------------------------|--|------------|-----|---------------------|-------|
| t _{PHL} , t _{PLH} | Maximum Propagation Delay, any P or Q to Output | | 21 | 30 | ns |
| t _{PLH} , t _{PHL} | Maximum Propagation Delay, Enable to any Output | | 14 | 20 | ns |

AC Electrical Characteristics

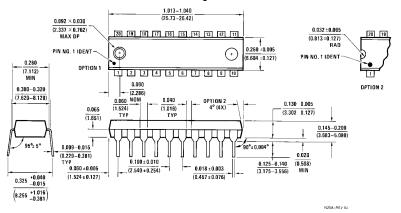
 V_{CC} =2.0V to 6.0V, C_L =50 pF, t_r = t_f =6 ns (unless otherwise specified)

| Symbol | Parameter | Conditions | v _{cc} | T _A = 25°C | | 74HC T _A = -40 to 85°C | 54HC T _A = -55 to 125°C | Units |
|-------------------------------------|---|------------|----------------------|-----------------------|-----------------|--------------------------------------|---------------------------------------|----------------|
| | | | | Typ Guaranteed Limits | | | | |
| t _{PHL} , t _{PLH} | Maximum Propagation Delay, P or Q to Output | | 2.0V 4.5V 6.0V | 60 22 19 | 175 35 30 | 220 44 38 | 263 53 45 | ns ns ns |
| t _{PHL} , t _{PLH} | Maximum Propagation Delay, Enable to Output | | 2.0V 4.5V 6.0V | 45 15 13 | 120 24 20 | 150 30 25 | 180 36 30 | ns ns ns |
| t _{THL} , t _{TLH} | Maximum Output Rise and Fall Time | | 2.0V 4.5V 6.0V | 30 8 7 | 75 15 13 | 95 19 16 | 110 22 19 | ns ns ns |
| C _{PD} | Power Dissipation Capacitance (Note 5) | | | 45 | | | | pF |
| C _{IN} | Maximum Input Capacitance | | | 5 | 10 | 10 | 10 | pF |

Note 5: C_{PD} determines the no load dynamic power consumption, $P_D = C_{PD} \ V_{CC}^2 \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$, and the no load dynamic current consumption, $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC}$, and $I_S = C_{PD} \ V_{CC} \ f + I_{CC} \ V_{CC} \ f + I_{CC}$



Order Number MM54HC521J or MM74HC521J NS Package J20A



Order Number MM74HC521N NS Package N20A

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